MOSFETs Silicon N-Channel MOS

# SSM3K339R

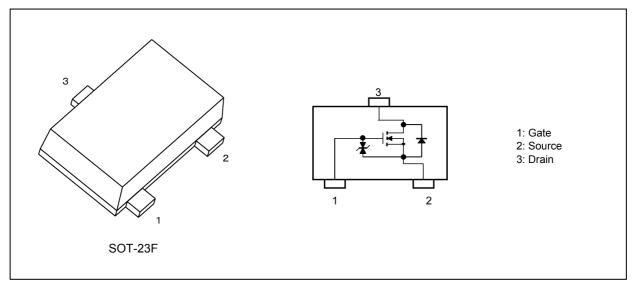
#### 1. Applications

- Power Management Switches
- DC-DC Converters

#### 2. Features

- (1) 1.8-V gate drive voltage.
- (2) Low drain-source on-resistance
  - :  $\mathrm{R}_{\mathrm{DS(ON)}}$  = 145 mΩ (typ.) (@V\_{\mathrm{GS}} = 8.0 V,  $\mathrm{I}_{\mathrm{D}}$  = 1.0 A)
  - $\mathrm{R}_{\mathrm{DS(ON)}}$  = 155 mO (typ.) (@V\_{\mathrm{GS}} = 4.5 V,  $\mathrm{I_{D}}$  = 1.0 A)
  - $\mathrm{R}_{\mathrm{DS(ON)}}$  = 160 m $\Omega$  (typ.) (@V\_{\mathrm{GS}} = 3.6 V,  $\mathrm{I_{D}}$  = 1.0 A)
  - $\mathrm{R}_{\mathrm{DS(ON)}}$  = 180 m $\Omega$  (typ.) (@V\_{\mathrm{GS}} = 2.5 V,  $\mathrm{I_{D}}$  = 0.5 A)
  - $\mathrm{R}_{\mathrm{DS(ON)}}$  = 220 m $\Omega$  (typ.) (@V\_{\mathrm{GS}} = 1.8 V,  $\mathrm{I}_{\mathrm{D}}$  = 0.2 A)

#### 3. Packaging and Pin Assignment



### 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, T<sub>a</sub> = 25 °C)

	Characteristics			Symbol	Rating	Unit
Drain-source voltage				V <sub>DSS</sub>	40	V
Gate-source voltage				V <sub>GSS</sub>	±12	
Drain current (DC)			(Note 1)	Ι <sub>D</sub>	2.0	А
Drain current (pulsed)			(Note 1), (Note 2)	I <sub>DP</sub>	4.0	
Power dissipation			(Note 3)	PD	1	W
Power dissipation		(t = 10 s)	(Note 3)		2	
Channel temperature				T <sub>ch</sub>	150	°C
Storage temperature				T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW)  $\leq$  10 ms, duty  $\leq$  1%
- Note 3: Device mounted on an FR4 board. (25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm ,Cu pad: 645 mm²)
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 5. Electrical Characteristics

#### 5.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = 1mA, V <sub>GS</sub> = 0 V	40	_	_	V
Drain-source breakdown voltage		V <sub>(BR)DSX</sub>	I <sub>D</sub> = 1mA, V <sub>GS</sub> = -12 V	25		_	
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V			1	μA
Gate leakage current		I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 10 V		_	10	
Gate threshold voltage	(Note 1)	V <sub>th</sub>	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 1mA	_	0.85	1.2	V
Drain-source on-resistance	(Note 2)	R <sub>DS(ON)</sub>	I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 8.0 V	_	145	185	mΩ
			I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 4.5 V		155	198	
			I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 4.2 V		156	201	
			I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 3.6 V		160	208	
			I <sub>D</sub> = 0.5 A, V <sub>GS</sub> = 2.5 V		180	238	
			I <sub>D</sub> = 0.2 A, V <sub>GS</sub> = 1.8 V	_	220	390	
Forward transfer admittance	(Note 2)	Y <sub>fs</sub>	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 0.2 A		2	_	S

Note 1: Let V<sub>th</sub> be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (1 mA for this device). Then, for normal switching operation, V<sub>GS(ON)</sub> must be higher than V<sub>th</sub>, and V<sub>GS(OFF)</sub> must be lower than V<sub>th</sub>. This relationship can be expressed as: V<sub>GS(OFF)</sub> < V<sub>th</sub> < V<sub>GS(ON)</sub>. Take this into consideration when using the device.

Note 2: Pulse measurement.

### 5.2. Dynamic Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance		V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V,	_	130	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	—	7.5	_	
Output capacitance	C <sub>oss</sub>		_	26	—	
Switching time (turn-on time)		V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.5 A,	_	13	_	ns
Switching time (turn-off time)	t <sub>off</sub>	$V_{GS}$ = 0 to 2.5 V, $R_{G}$ = 4.7 $\Omega$	_	8		

#### 5.3. Switching Time Test Circuit

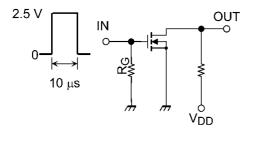


Fig. 5.3.1 Switching Time Test Circuit

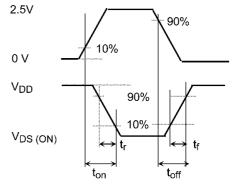


Fig. 5.3.2 Input Waveform/Output Waveform

#### 5.4. Gate Charge Characteristics (Unless otherwise specified, $T_a = 25$ °C)

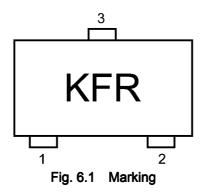
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.8 A,	—	1.1	—	nC
Gate-source charge 1	Q <sub>gs1</sub>	V <sub>GS</sub> = 4.2 V	_	0.18	_	
Gate-drain charge	Q <sub>gd</sub>		_	0.5	_	

### 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25$ °C)

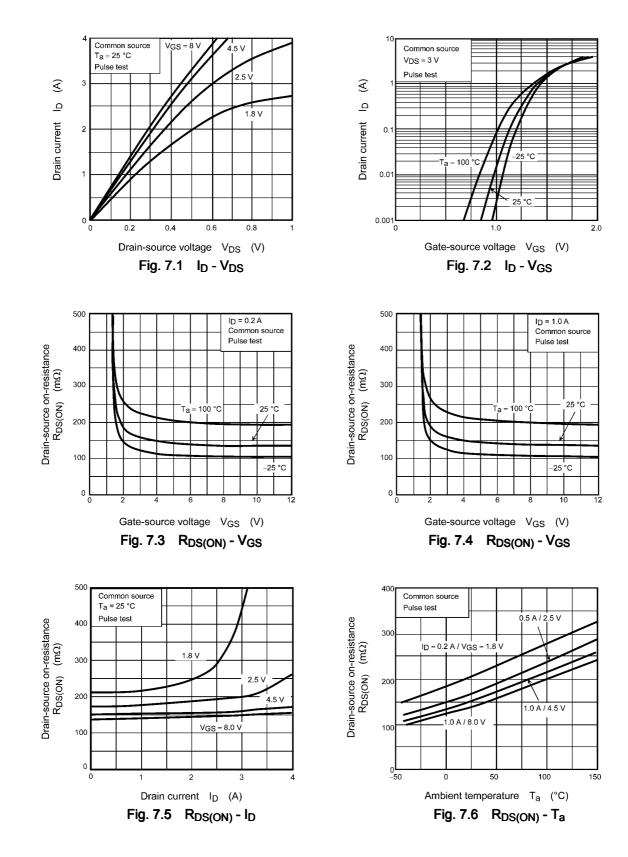
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage (No	ote 1)	$V_{\text{DSF}}$	$I_{\rm D}$ = -2 A, $V_{\rm GS}$ = 0 V		-0.85	-1.2	V

Note 1: Pulse measurement.

### 6. Marking



### 7. Characteristics Curves (Note)



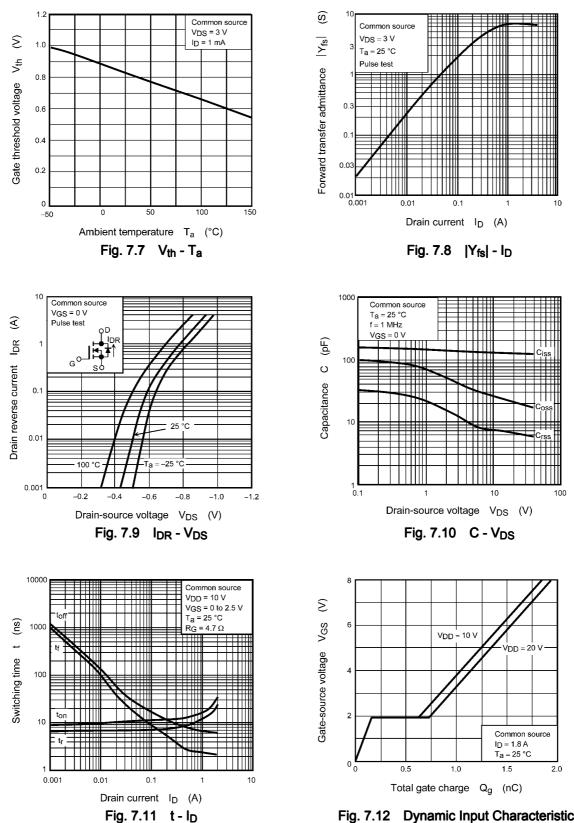
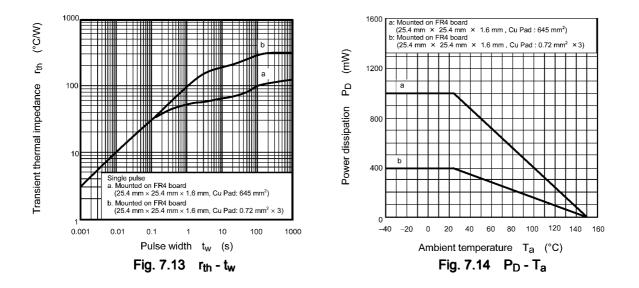


Fig. 7.12 Dynamic Input Characteristics



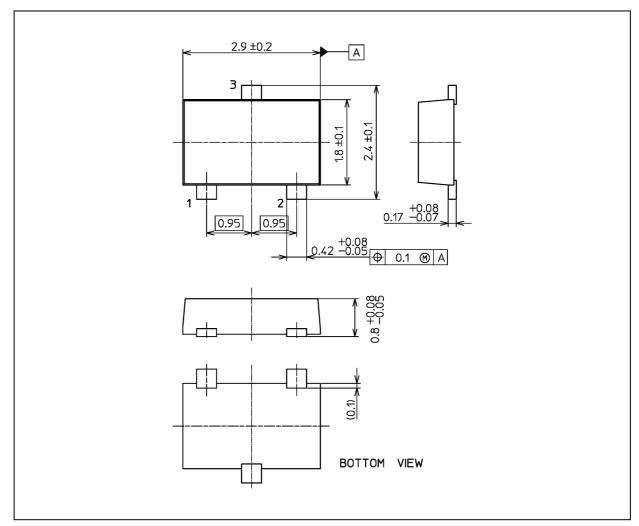
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### SSM3K339R

### Package Dimensions

Unit: mm



Weight: 0.011 g (typ.)

	Package Name(s)
Nickname: SOT-23F	

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